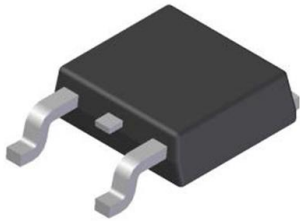


# ZXMN10A25K Datasheet

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<https://www.DiGi-Electronics.com>

DiGi Electronics Part Number	ZXMN10A25K-DG
Manufacturer	<a href="#">Diodes Incorporated</a>
Manufacturer Product Number	ZXMN10A25K
Description	MOSFET N-CH 100V 4.2A TO252-3
Detailed Description	N-Channel 100 V 4.2A (Ta) 2.11W (Ta) Surface Mount TO-252-3



Tel: +00 852-30501935

RFQ Email: [Info@DiGi-Electronics.com](mailto:Info@DiGi-Electronics.com)

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## Purchase and inquiry

Manufacturer Product Number:

ZXMN10A25K

Series:

-

FET Type:

N-Channel

Drain to Source Voltage (Vdss):

100 V

Drive Voltage (Max Rds On, Min Rds On):

6V, 10V

Vgs(th) (Max) @ Id:

4V @ 250 $\mu$ A

Vgs (Max):

$\pm$ 20V

FET Feature:

-

Operating Temperature:

-55°C ~ 150°C (Tj)

Supplier Device Package:

TO-252-3

Manufacturer:

Diodes Incorporated

Product Status:

Obsolete

Technology:

MOSFET (Metal Oxide)

Current - Continuous Drain (Id) @ 25°C:

4.2A (Ta)

Rds On (Max) @ Id, Vgs:

125mOhm @ 2.9A, 10V

Gate Charge (Qg) (Max) @ Vgs:

17.16 nC @ 10 V

Input Capacitance (Ciss) (Max) @ Vds:

859 pF @ 50 V

Power Dissipation (Max):

2.11W (Ta)

Mounting Type:

Surface Mount

Package / Case:

TO-252-3, DPAK (2 Leads + Tab), SC-63

## Environmental & Export classification

RoHS Status:

ROHS3 Compliant

REACH Status:

REACH Unaffected

HTSUS:

8541.29.0095

Moisture Sensitivity Level (MSL):

1 (Unlimited)

ECCN:

EAR99

## 100V N-CHANNEL ENHANCEMENT MODE MOSFET

## Product Summary

$V_{(BR)DSS}$	$R_{DS(ON)}$	Package	Max $I_D$ $T_A = +25^\circ C$
100V	125m $\Omega$ @ $V_{GS} = 10V$	TO252 (DPAK)	6.4A
	150m $\Omega$ @ $V_{GS} = 6V$		5.8A

## Description

This MOSFET has been designed to minimize the on-state resistance ( $R_{DS(on)}$ ) and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

## Applications

- DC-DC Converters
- Power Management Functions
- Disconnect Switches
- Motor Control

## Features

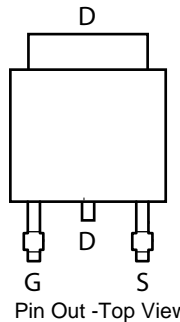
- Low On-Resistance
- Fast Switching Speed
- Low Gate Drive
- **Lead-Free Finish; RoHS Compliant (Notes 1 & 2)**
- **Halogen and Antimony Free. "Green" Device (Note 3)**
- **Qualified to AEC-Q101 Standards for High Reliability**

## Mechanical Data

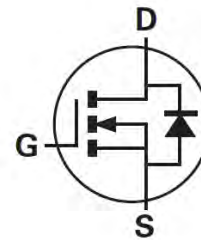
- Case: TO252 (DPAK)
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0 (Note 1)
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Matte Tin Finish annealed over Copper leadframe. Solderable per MIL-STD-202, Method 208
- Weight: 0.33 grams (approximate)



Top View



Pin Out -Top View



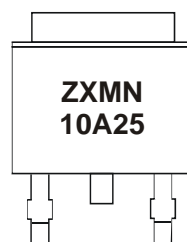
Equivalent Circuit

## Ordering Information (4 & 5)

Part Number	Marking	Reel size (inches)	Tape width (mm)	Quantity per reel
ZXMN10A25KTC	ZXMN10A25	13	16	2,500

- Notes:
1. EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant. All applicable RoHS exemptions applied.
  2. See <http://www.diodes.com> for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
  3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
  4. For Packaging Details, go to our website at <http://www.diodes.com>.
  5. Products with Q-suffix are automotive grade. Automotive products are electrical and thermal the same as the commercial, except where specified.

## Marking Information



ZXMN10A25 = Product Type Marking Code


**ZXMN10A25K**
**Maximum Ratings** (@ $T_A = +25^\circ\text{C}$ , unless otherwise specified.)

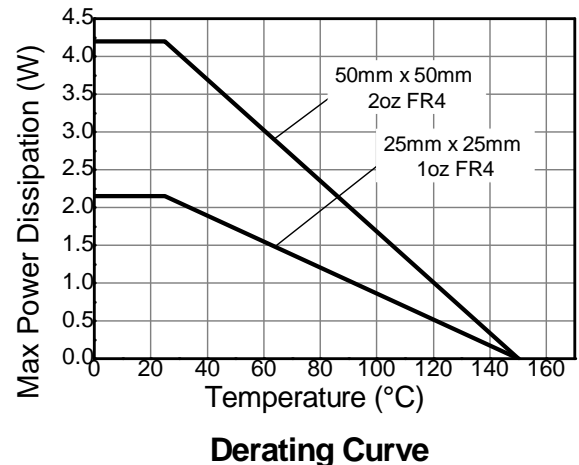
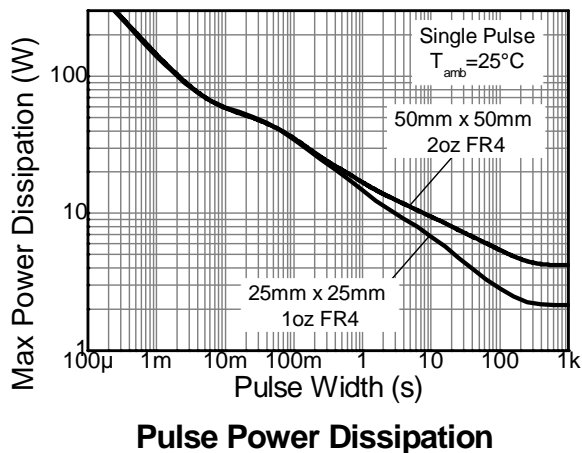
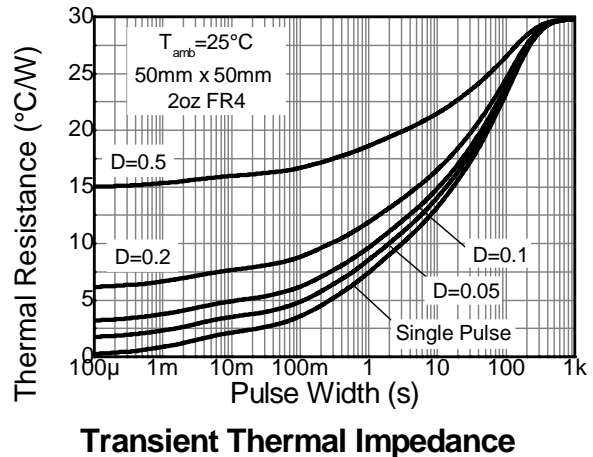
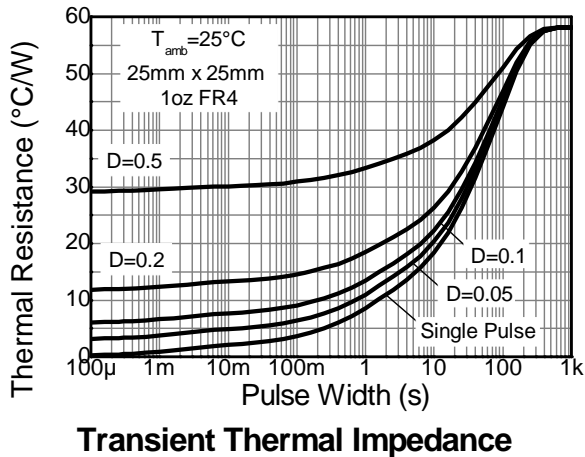
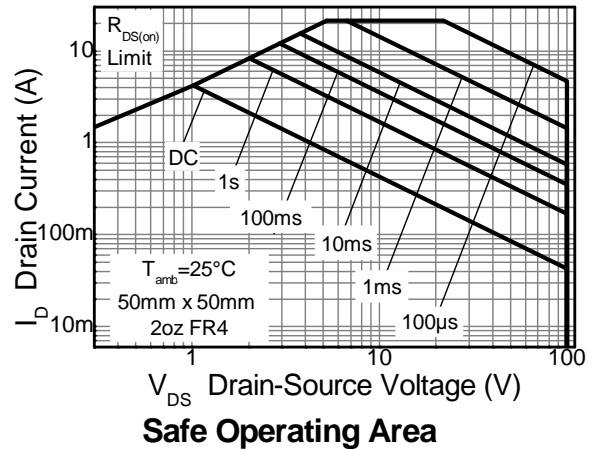
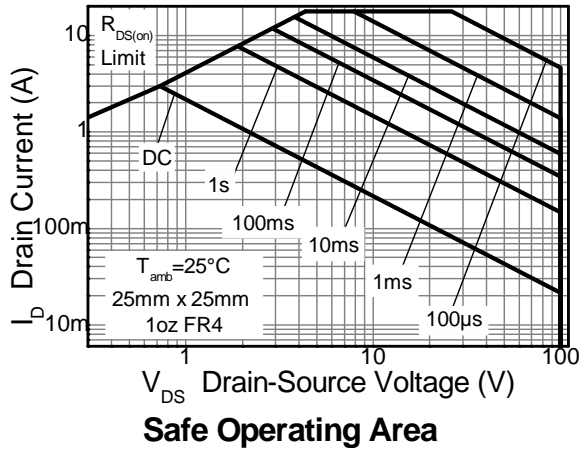
Characteristic		Symbol	Value	Unit
Drain-Source voltage		$V_{DS}$	100	V
Gate-Source voltage		$V_{GS}$	$\pm 20$	V
Continuous Drain current	$V_{GS} = 10\text{V}$	(Note 7)	6.4	A
		$T_A = +70^\circ\text{C}$ (Note 7)	5	
		(Note 6)	4.2	
Pulsed Drain current		$I_{DM}$	21	A
Continuous Source current (Body diode)		$I_S$	10	A
Pulsed Source current (Body diode)		$I_{SM}$	21	A

**Thermal Characteristics**

Characteristic		Symbol	Value	Unit
Power dissipation Linear derating factor	(Note 6)	$P_D$	4.25	W mW/ $^\circ\text{C}$
			34	
	(Note 7)		9.85	
			78.7	
Thermal Resistance, Junction to Ambient	(Note 9)	$R_{\theta JA}$	2.11	$^\circ\text{C/W}$
			16.8	
	(Note 6)		29.4	
	(Note 7)		12.7	
	(Note 9)		59.1	
Thermal Resistance, Junction to Lead		$R_{\theta JL}$	1.43	
Operating and storage temperature range		$T_J, T_{STG}$	-55 to 150	$^\circ\text{C}$

- Notes:
6. For a device surface mounted on 50mm x 50mm x 1.6mm FR4 PCB with high coverage of single sided 2oz copper, in still air conditions; the device is measured when operating in a steady-state condition.
  7. For a device surface mounted on FR4 PCB measured at  $t \leq 10$  sec.
  8. Repetitive rating 50mm x 50mm x 1.6mm FR4 PCB,  $D = 0.02$  and pulse width 300 $\mu\text{s}$ . The pulse current is limited by the maximum junction temperature.
  9. For a device surface mounted on 25mm x 25mm x 1.6mm FR4 PCB with high coverage of single sided 1oz copper, in still air conditions; the device is measured when operating in a steady-state condition.
  10. Thermal resistance from junction to solder-point (at the end of the drain lead).

**Thermal Characteristics**




**ZXMN10A25K**
**Electrical Characteristics** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

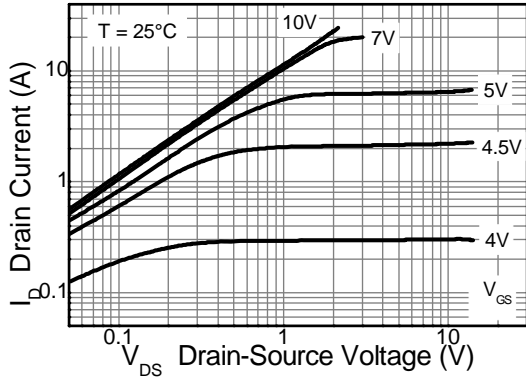
Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition	
<b>OFF CHARACTERISTICS</b>							
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	100	—	—	V	I <sub>D</sub> = 250μA, V <sub>GS</sub> = 0V	
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	—	—	0.5	μA	V <sub>DS</sub> = 100V, V <sub>GS</sub> = 0V	
Gate-Source Leakage	I <sub>GSS</sub>	—	—	±100	nA	V <sub>GS</sub> = ±20V, V <sub>DS</sub> = 0V	
<b>ON CHARACTERISTICS</b>							
Gate Threshold Voltage	V <sub>GS(th)</sub>	2.0	—	4.0	V	I <sub>D</sub> = 250μA, V <sub>DS</sub> = V <sub>GS</sub>	
Static Drain-Source On-Resistance (Note 11)	R <sub>DS(on)</sub>	—	—	125	mΩ	V <sub>GS</sub> = 10V, I <sub>D</sub> = 3.2A	
				150		V <sub>GS</sub> = 6V, I <sub>D</sub> = 2.6A	
Forward Transconductance (Notes 11 & 12)	g <sub>fs</sub>	—	7.3	—	S	V <sub>DS</sub> = 15V, I <sub>D</sub> = 2.9A	
Diode Forward Voltage (Note 11)	V <sub>SD</sub>	—	0.85	0.95	V	I <sub>S</sub> = 3.2A, V <sub>GS</sub> = 0V, T <sub>J</sub> = +25°C	
Reverse recovery time (Note 12)	t <sub>rr</sub>	—	40.5	—	ns	I <sub>S</sub> = 2.9A, di/dt = 100A/μs	
Reverse recovery charge (Note 12)	Q <sub>rr</sub>	—	62	—	nC	T <sub>J</sub> = +25°C	
<b>DYNAMIC CHARACTERISTICS (Note 12)</b>							
Input Capacitance	C <sub>iss</sub>	—	859	—	pF	V <sub>DS</sub> = 50V, V <sub>GS</sub> = 0V f = 1MHz	
Output Capacitance	C <sub>oss</sub>	—	57.3	—	pF		
Reverse Transfer Capacitance	C <sub>rss</sub>	—	33	—	pF		
Total Gate Charge (Note 13)	Q <sub>g</sub>	—	9.6	—	nC	V <sub>GS</sub> = 5V	V <sub>DS</sub> = 50V I <sub>D</sub> = 2.9A
Total Gate Charge (Note 13)	Q <sub>g</sub>	—	17.16	—	nC	V <sub>GS</sub> = 10V	
Gate-Source Charge (Note 13)	Q <sub>gs</sub>	—	3.77	—	nC		
Gate-Drain Charge (Note 13)	Q <sub>gd</sub>	—	5.36	—	nC		
Turn-On Delay Time (Note 13)	t <sub>D(on)</sub>	—	4.9	—	ns	V <sub>DD</sub> = 50V, V <sub>GS</sub> = 10V I <sub>D</sub> = 1A, R <sub>G</sub> ≅ 6.0Ω	
Turn-On Rise Time (Note 13)	t <sub>r</sub>	—	3.7	—	ns		
Turn-Off Delay Time (Note 13)	t <sub>D(off)</sub>	—	17.7	—	ns		
Turn-Off Fall Time (Note 13)	t <sub>f</sub>	—	9.4	—	ns		

- Notes:
11. Measured under pulsed conditions. Pulse width ≤ 300μs; duty cycle ≤ 2%
  12. For design aid only, not subject to production testing.
  13. Switching characteristics are independent of operating junction temperatures.

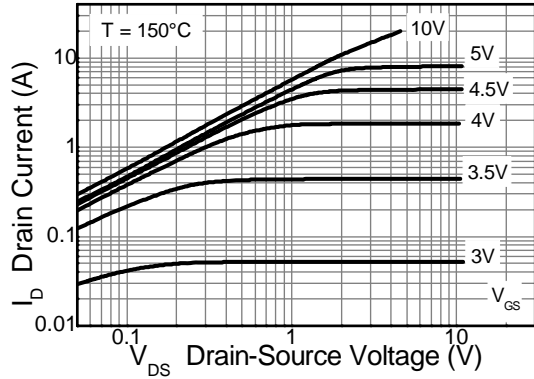


**ZXMN10A25K**

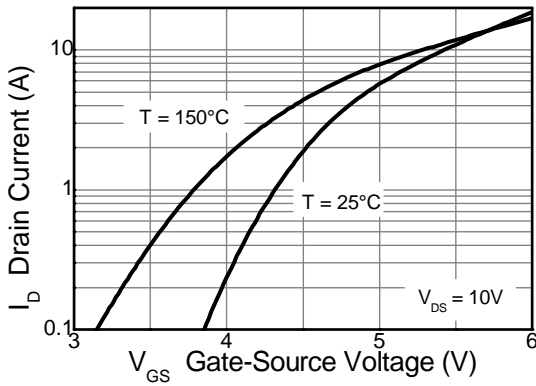
**Typical Characteristics**



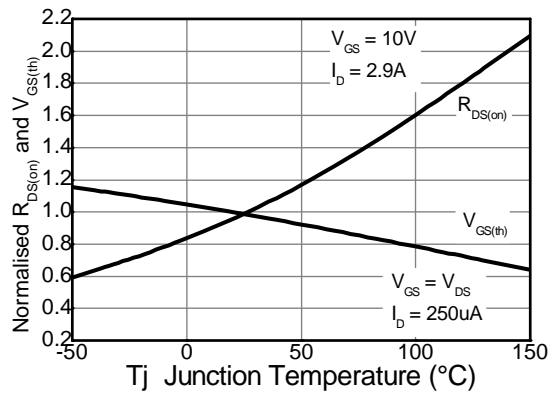
**Output Characteristics**



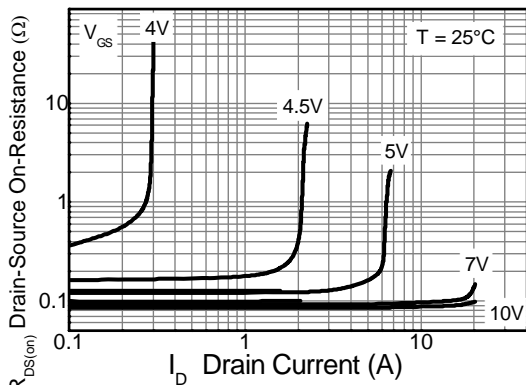
**Output Characteristics**



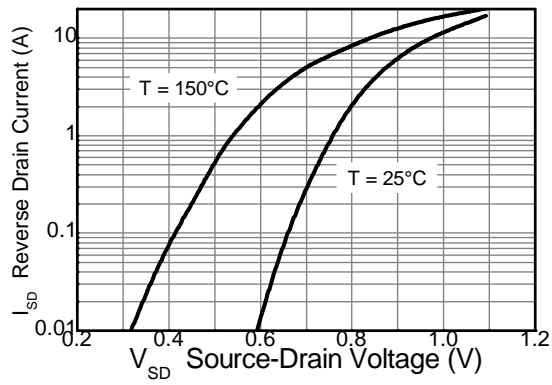
**Typical Transfer Characteristics**



**Normalised Curves v Temperature**

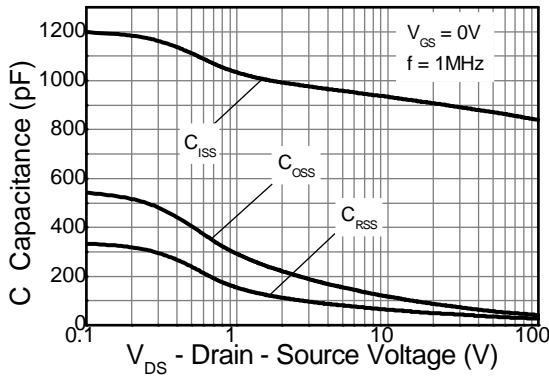


**On-Resistance v Drain Current**

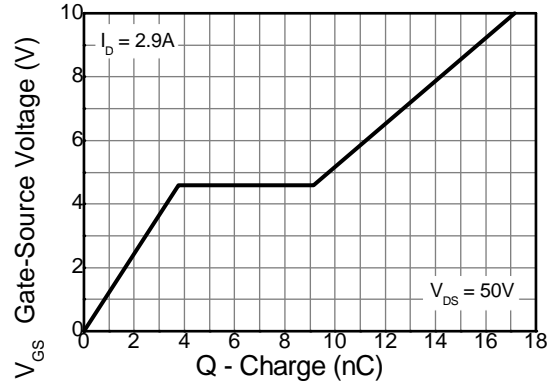


**Source-Drain Diode Forward Voltage**

**Typical Characteristics (cont.)**

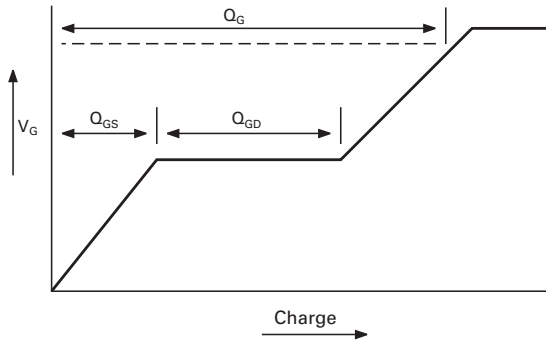


**Capacitance v Drain-Source Voltage**

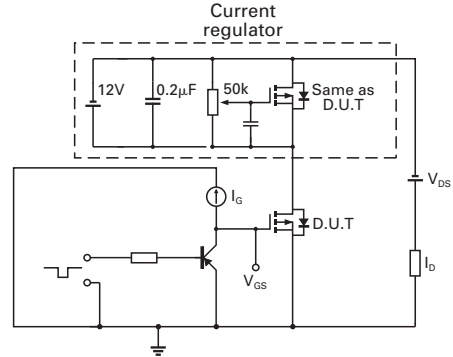


**Gate-Source Voltage v Gate Charge**

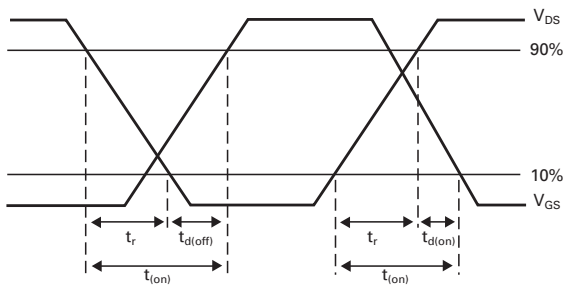
**Test Circuits**



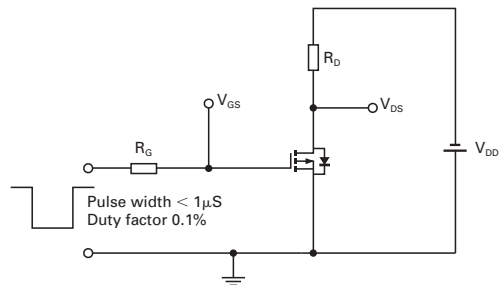
**Basic gate charge waveform**



**Gate charge test circuit**



**Switching time waveforms**

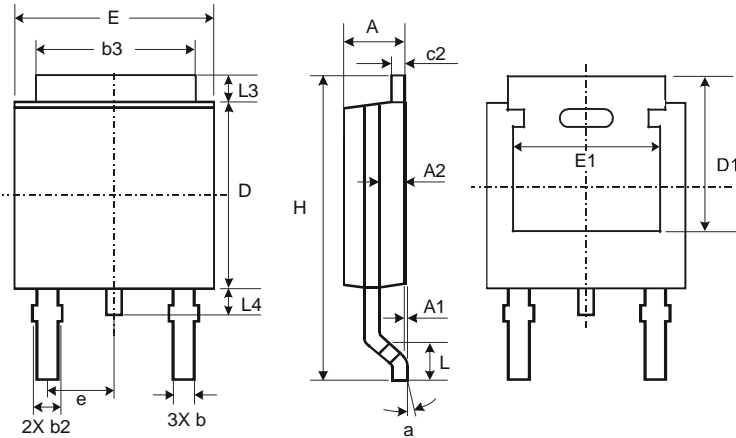


**Switching time test circuit**



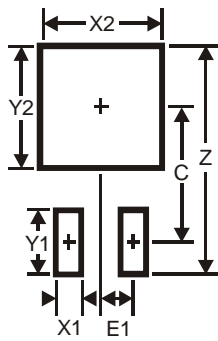
**ZXMN10A25K**

**Package Outline Dimensions**



TO252			
Dim	Min	Max	Typ
A	2.19	2.39	2.29
A1	0.00	0.13	0.08
A2	0.97	1.17	1.07
b	0.64	0.88	0.783
b2	0.76	1.14	0.95
b3	5.21	5.46	5.33
c2	0.45	0.58	0.531
D	6.00	6.20	6.10
D1	5.21	-	-
e	-	-	2.286
E	6.45	6.70	6.58
E1	4.32	-	-
H	9.40	10.41	9.91
L	1.40	1.78	1.59
L3	0.88	1.27	1.08
L4	0.64	1.02	0.83
a	0°	10°	-
All Dimensions in mm			

**Suggested Pad Layout**



Dimensions	Value (in mm)
Z	11.6
X1	1.5
X2	7.0
Y1	2.5
Y2	7.0
C	6.9
E1	2.3

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